

Micron Leads PSRAM Market with Sample Availability of First 128 Megabit Burst CellularRAM Device

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First 128Mb Burst 1.5 Generation CellularRAM Device Manufactured on Micron's Award-Winning 6F² Array Architecture

[Micron Technology, Inc.](#)

, today announced sample availability of the first 128 Megabit (Mb), burst CellularRAM™ device incorporating the new 1.5 generation feature set. Availability of this device is significant as it is one of the first 128Mb burst pseudo-static RAMs (PSRAMs) currently available in the market, and because it represents another memory architecture Micron successfully produced with the Company's revolutionary 6F² array architecture technology.

“Growth of our CellularRAM business is exceeding expectations, and we continue to see PSRAM displace traditional asynchronous SRAM in the rapidly growing handset market,” said Dan Skinner, Micron's Mobile DRAM Product Marketing Manager. “Micron demonstrated our technology leadership with the production of the first generation of CellularRAM products on our advanced 110 nanometer (nm) DRAM process. Now, Micron is leading the industry again, developing the first 128Mb variable latency burst mode CellularRAM device, and producing this product on our award-winning 6F² array architecture technology. This is truly a remarkable achievement, and an exciting example of Micron's ability to leverage our expertise in DRAM product and process

technology to support new and emerging markets.”

Micron’s 128Mb burst CellularRAM devices target mobile handsets providing performance enhancing features. The cell architecture used to produce this device minimizes standby and active current levels resulting in a lower power, higher bandwidth solution than competing PSRAM technologies. Other unique performance features include the ability to perform READs and WRITEs in 4, 8, 16, 32-word or continuous bursts, increased compatibility with flash burst protocol, burst clock rates of 104/80/66 MHz, and a variable latency function that minimizes delays and maximizes bandwidth. In addition, the CellularRAM specification co-development members defined a common bond format allowing multichip package (MCP) manufacturers to utilize multiple vendors without requiring a redesign of their substrates.

Micron Technology, Inc., is one of the world's leading providers of advanced semiconductor solutions. Through its worldwide operations, Micron manufactures and markets DRAMs, Flash memory, CMOS image sensors, other semiconductor components and memory modules for use in leading-edge computing, consumer, networking, and mobile products. Micron's common stock is traded on the New York Stock Exchange (NYSE) under the MU symbol. To learn more about Micron Technology, Inc., visit its web site at www.micron.com.

The original press release can be found [here](#).

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